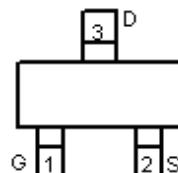


-30V(D-S) P-Channel Enhancement Mode Power MOS FET

General Features

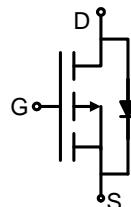
- $V_{DS} = -30V, I_D = -2.0A$
- $R_{DS(ON)} < 130m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} < 180m\Omega @ V_{GS}=-4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

**Lead Free**

Marking and pin assignment

PIN Configuration

SOT-23 top view



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
	MSP2303	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-2.0	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1.0	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	125	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-2.0\text{A}$	-	72	130	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-1.5\text{A}$	-	110	180	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-2\text{A}$		2	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	226	-	PF
Output Capacitance	C_{oss}		-	47	-	PF
Reverse Transfer Capacitance	C_{rss}		-	28	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-15\text{V}, R_{\text{L}}=15\Omega, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=6\Omega$	-	9	-	nS
Turn-on Rise Time	t_{r}		-	9	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	18	-	nS
Turn-Off Fall Time	t_{f}		-	6	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-2.0\text{A}, V_{\text{GS}}=-10\text{V}$	-	8.5	-	nC
Gate-Source Charge	Q_{gs}		-	2.3	-	nC
Gate-Drain Charge	Q_{gd}		-	1.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=-2.0\text{A}$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

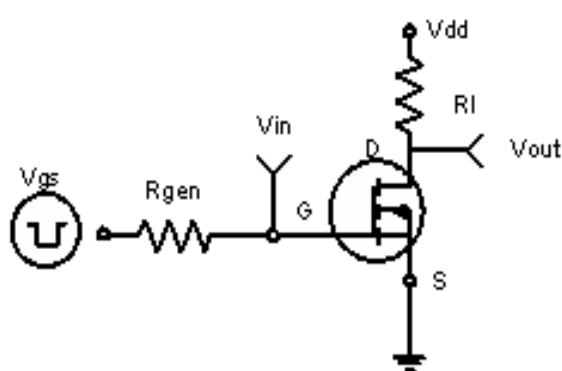


Figure 1:Switching Test Circuit

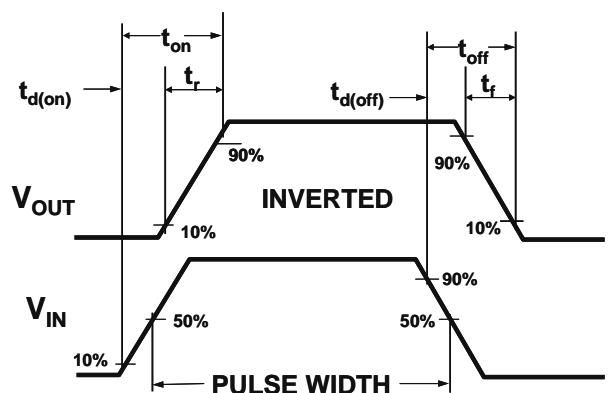


Figure 2:Switching Waveforms

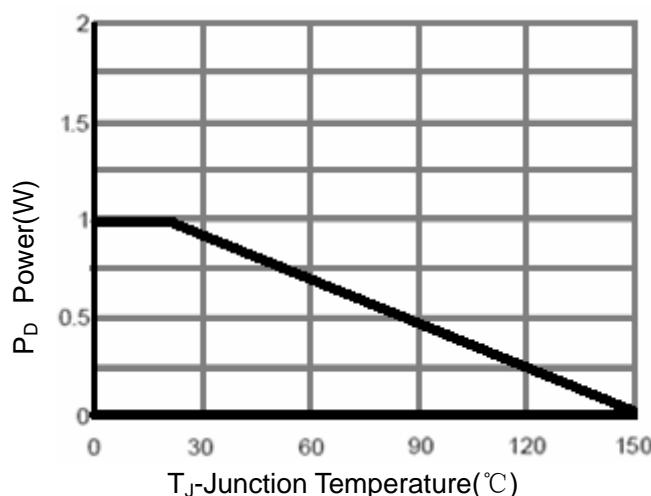


Figure 3 Power Dissipation

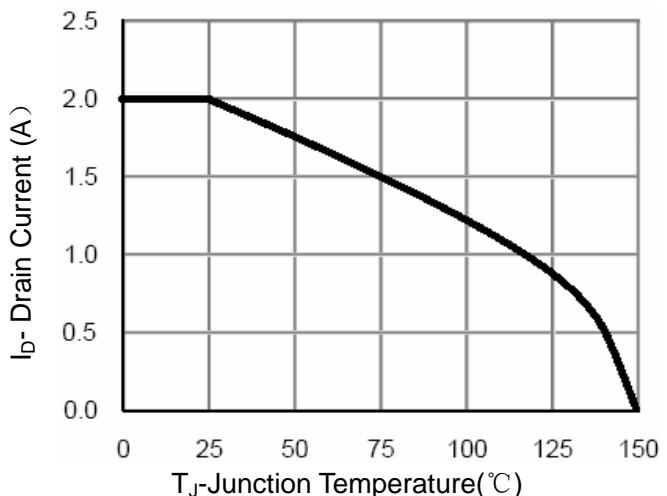


Figure 4 Drain Current

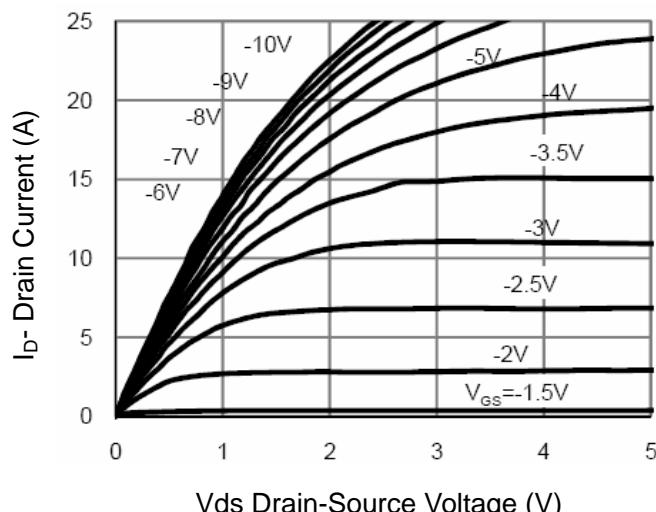


Figure 5 Output Characteristics

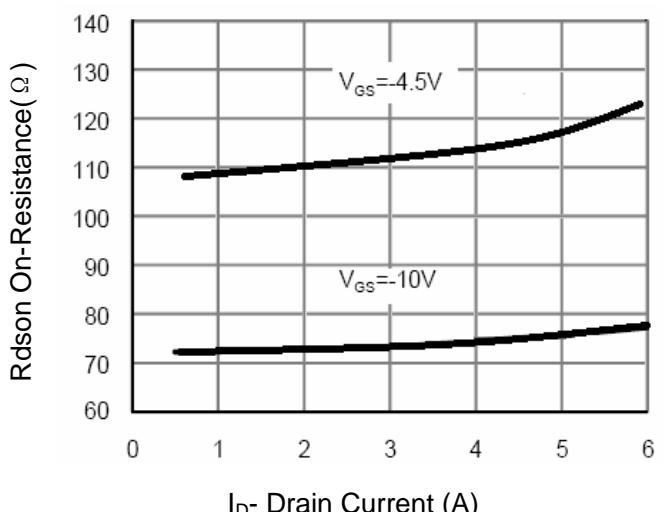
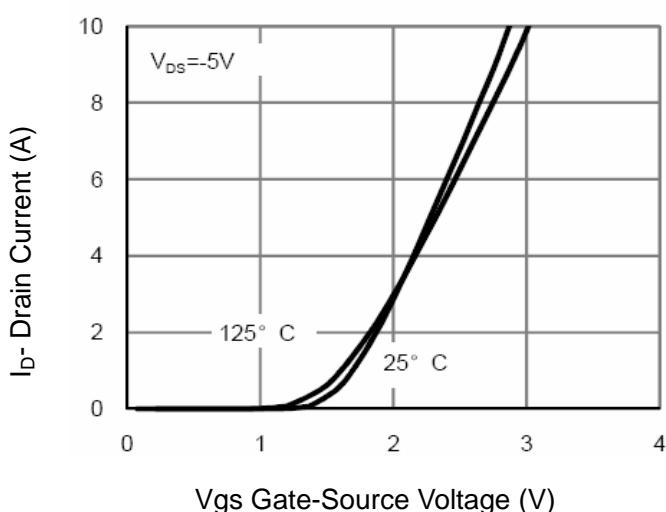
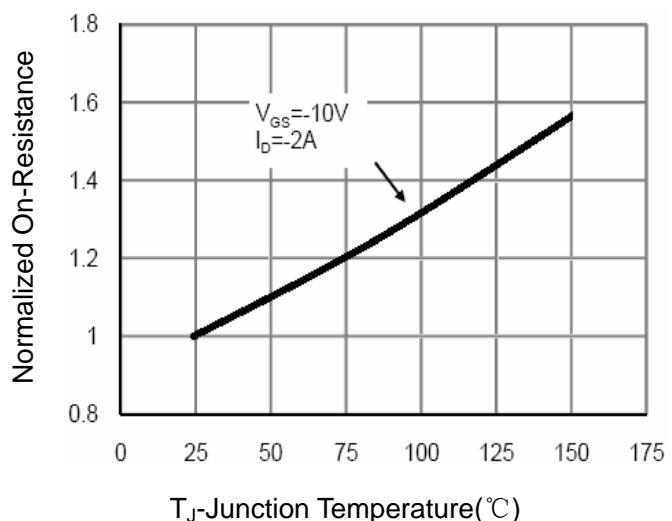
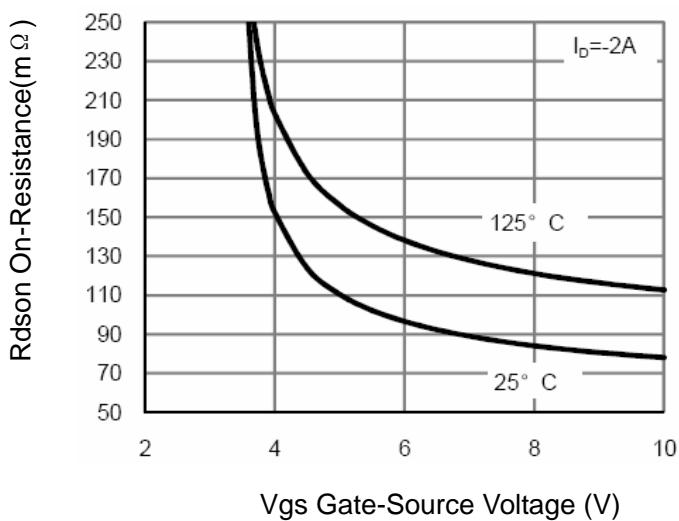
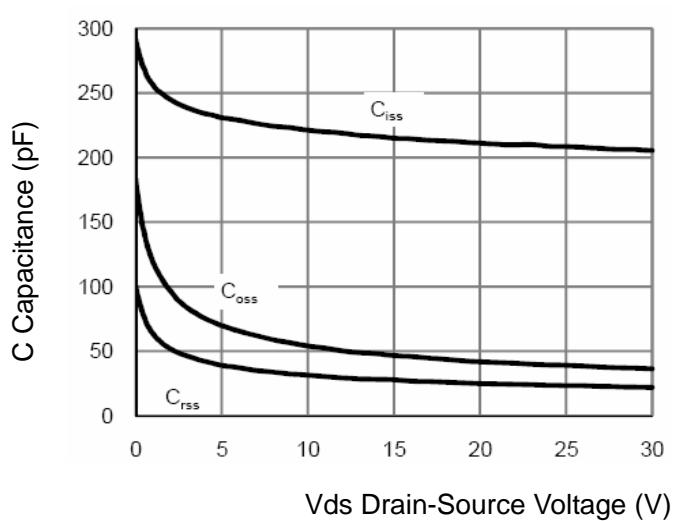
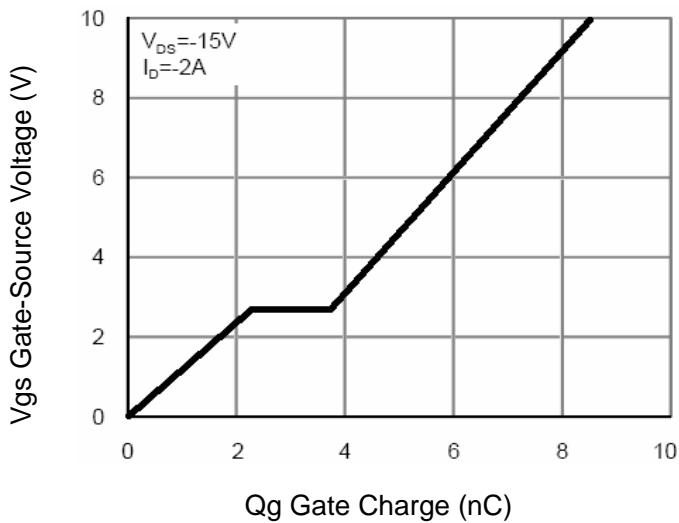
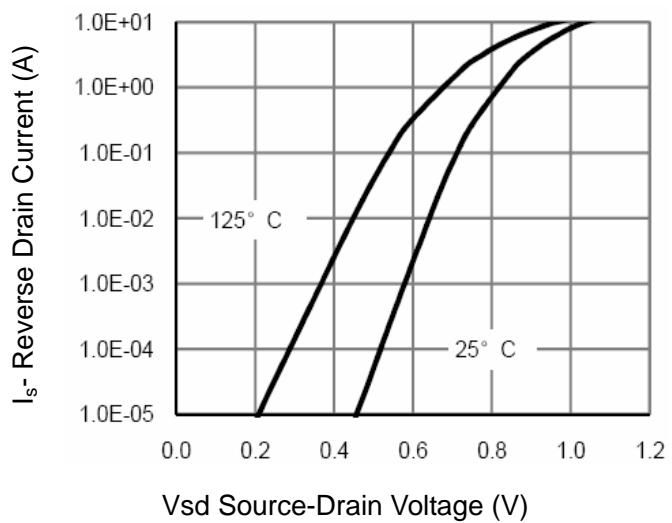


Figure 6 Drain-Source On-Resistance

**Figure 7 Transfer Characteristics****Figure 8 Drain-Source On-Resistance****Figure 9 $R_{DS(on)}$ vs V_{GS}** **Figure 10 Capacitance vs V_{DS}** **Figure 11 Gate Charge****Figure 12 Source-Drain Diode Forward**

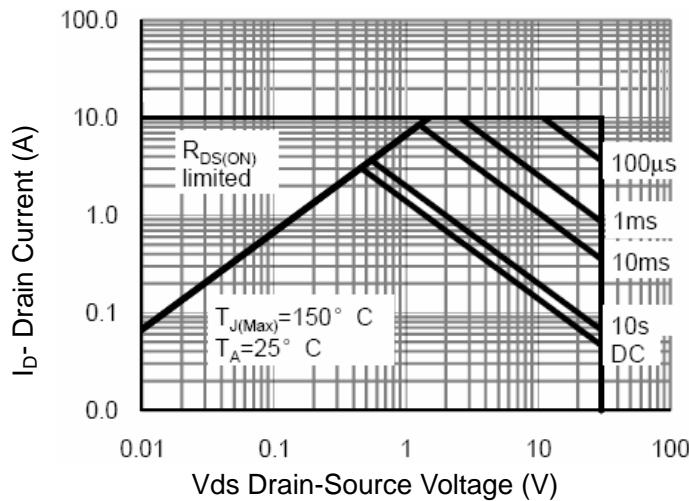


Figure 13 Safe Operation Area

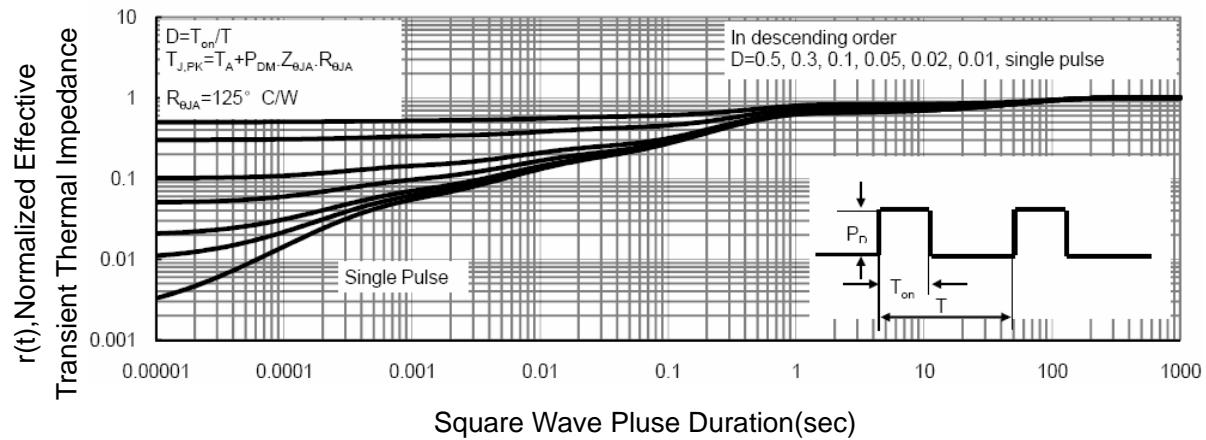
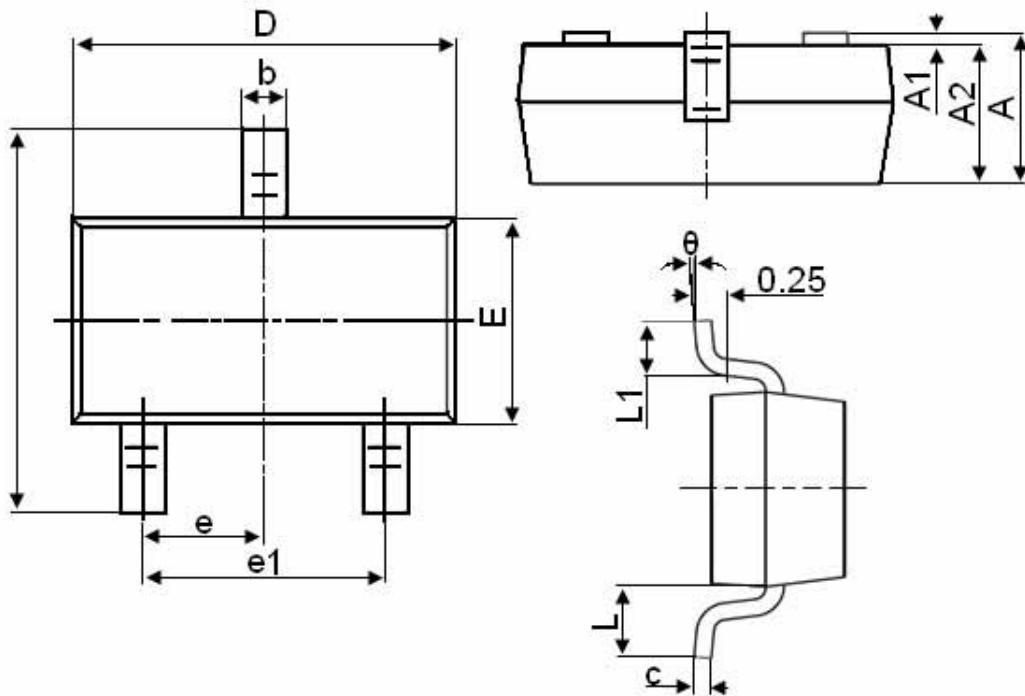


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.